



100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	RDS(ON) Max	I _D T _C = +25°C
100V	$222m\Omega$ @ $V_{GS} = 10V$	8.0A
	270mΩ @ $V_{GS} = 4.5V$	7.3A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Load Switch

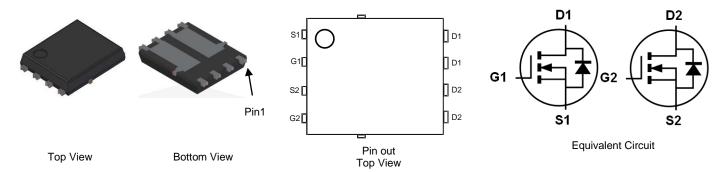
Features

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Wettable Flank for Improved Optical Inspections
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.097 grams (Approximate)

PowerDI5060-8 (SWP) (Type R)



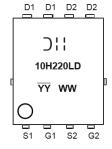
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN10H220LPDW-13	PowerDI5060-8 (SWP) (Type R)	2500 / Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



⊃¦¦ = Manufacturer's Marking
 10H220LD = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 19 = 2019)
 WW = Week (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	100	V	
Gate-Source Voltage		Vgss	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V $ T_C = +25^{\circ}C $ $T_C = +70^{\circ}C $		lo	8.0 6.4	А
Maximum Body Diode Forward Current (Note 6)	ls	8.0	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	32	A
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)		Ism	32	Α
Avalanche Current (Note 7)	L = 0.1mH	I _{AS}	4.7	A
Avalanche Energy (Note 7)	L = 0.1mH	Eas	1.1	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	P _D	2.2	W	
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	57	°C/W	
Thermal Resistance, Junction to Case (Note 6)	Rejc	5.8	- C/VV	
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

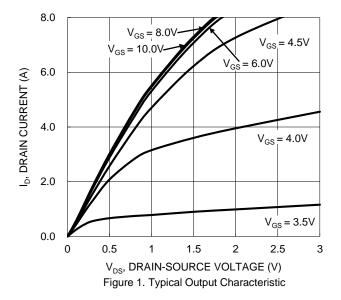
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BVDSS	100	_	_	V	V _G S = 0V, I _D = 250μA	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μA	V _{DS} = 100V, V _{GS} = 0V	
Gate-Source Leakage	Igss	_	_	100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	1	_	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Descous	_	168	222	mΩ	VGS = 10V, ID = 2A	
Static Drain-Source On-Nesistance	RDS(ON)	_	208	270	mΩ	Vgs = 4.5V, ID = 1A	
Diode Forward Voltage	VsD	_	0.8	1.3	V	Vgs = 0V, Is = 2A	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss		384			V _{DS} = 25V, f = 1MHz, V _{GS} = 0V	
Output Capacitance	Coss	_	23	_	pF		
Reverse Transfer Capacitance	Crss	_	17	_			
Gate Resistance	R _G	_	2.4	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	3.7	_			
Total Gate Charge (V _{GS} = 10V)	Qg	_	6.7	_	nC	V _{DD} = 50V, I _D = 1.6A	
Gate-Source Charge	Qgs	_	1.3	_	IIC	VDD = 50V, ID = 1.6A	
Gate-Drain Charge	Q _{gd}	_	2	_			
Turn-On Delay Time	tD(ON)	_	6.2	_			
Turn-On Rise Time	t _R	_	8.7	_		$V_{DD} = 50V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	7.4	_	ns	$R_G = 6.8\Omega$, $I_D = 1.0A$	
Turn-Off Fall Time	t _F		4.2				
Body Diode Reverse Recovery Time	trr	_	20	_	ns	La 1.10 dl/dt 1000/up	
Body Diode Reverse Recovery Charge	Qrr		11		nC	Is = 1.1A, dl/dt = 100A/µs	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

- 6. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.

DMN10H220LPDW
Document number: DS42085 Rev.2 - 2





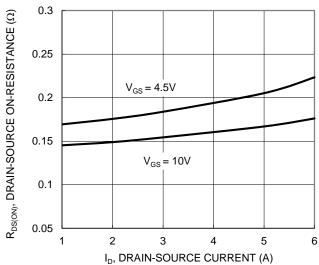


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

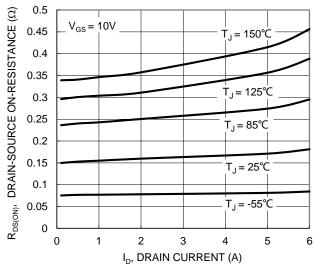
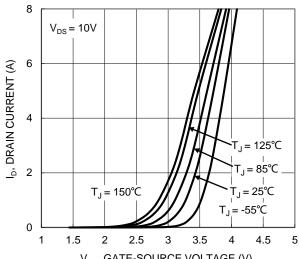


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic

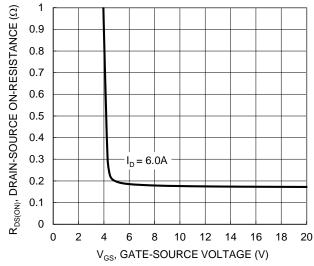


Figure 4. Typical Transfer Characteristic

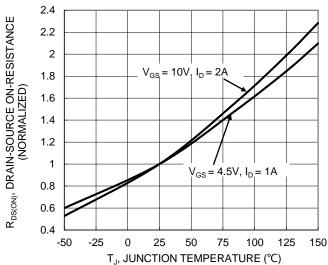


Figure 6. On-Resistance Variation with Junction Temperature





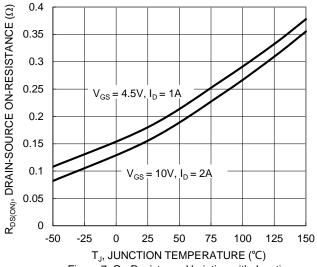


Figure 7. On-Resistance Variation with Junction Temperature

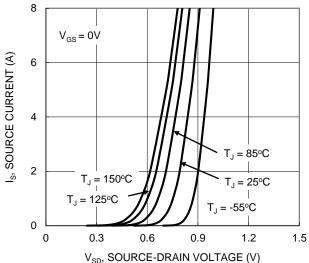


Figure 9. Diode Forward Voltage vs. Current

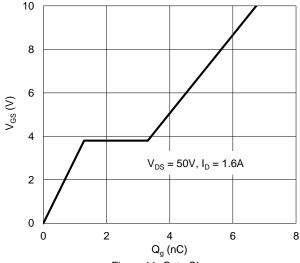


Figure 11. Gate Charge

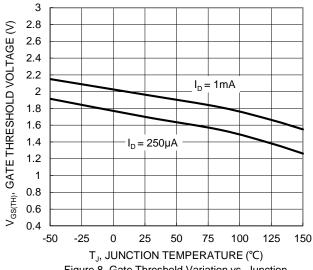
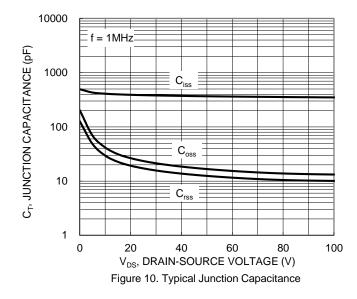


Figure 8. Gate Threshold Variation vs. Junction Temperature



100 R_{DS(ON)} Limited $P_W = 10\mu s$ 10 DRAIN CURRENT (A) $= 100 \mu s$ 1 $T_{J(Max)} = 150^{\circ}C$ 0.1 T_C = 25°C Single Pulse DUT on Infinite Heatsink $V_{GS} = 10V$ 0.01 0.1 10 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



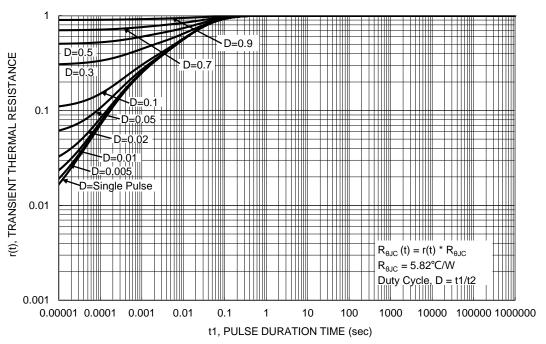


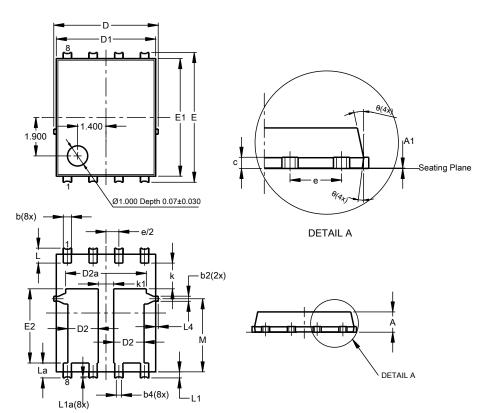
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Type R)

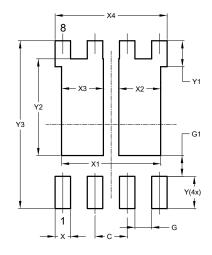


PowerDI5060-8 (SWP) (Type R)					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0	0.05			
b	0.30	0.50	0.41		
b2	0.20	0.35	0.25		
b4).25REI	F		
C	0.230	0.330	0.277		
D	5	.15 BS	O		
D1	4.70	5.10	4.90		
D2	1.40	1.60	1.50		
D2a	3.78	4.18	3.98		
Ε	6	.40 BS			
E1	5.60	6.00	5.80		
E2	3.46	3.86	3.66		
е	1.27BSC				
k	1.05				
k1	0.56				
L	0.635	0.835	0.735		
La	0.635	0.835	0.735		
L1	0.200	0.400	0.300		
L1a	0.050REF				
L4	0.025	0.225	0.125		
М	3.205	4.005	3.605		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Type R)



Dimensions	Value		
Dillicipions	(in mm)		
С	1.270		
G	0.660		
G1	0.820		
Х	0.610		
X1	3.910		
X2	1.650		
Х3	1.650		
X4	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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DMN10H220LPDW
Document number: DS42085 Rev.2 - 2

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